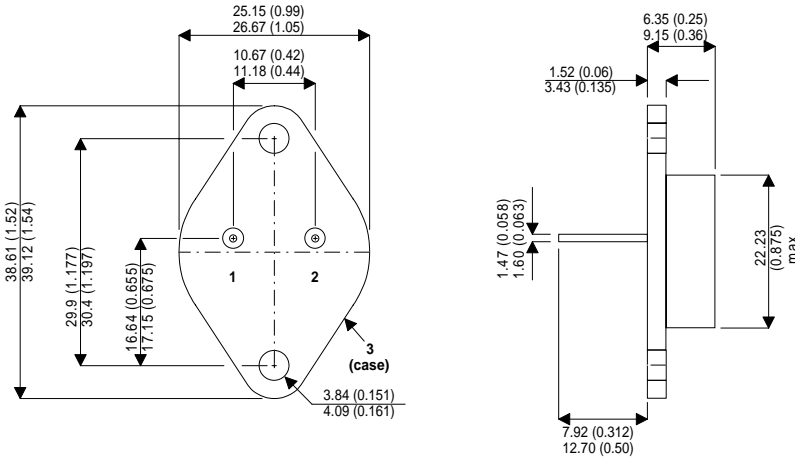


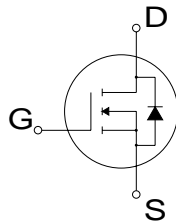
TO-3 Package Outline.
Dimensions in mm (inches)



Pin 1 – Gate

Pin 2 – Source

Case – Drain



**N-CHANNEL
ENHANCEMENT MODE
HIGH VOLTAGE
POWER MOSFETS**

V_{DSS} 500V
 $I_{D(cont)}$ 23A
 $R_{DS(on)}$ 0.20 Ω

- **Faster Switching**
- **Lower Leakage**
- **TO-3 Hermetic Package**

StarMOS is a new generation of high voltage N-Channel enhancement mode power MOSFETs. This new technology minimises the JFET effect, increases packing density and reduces the on-resistance. StarMOS also achieves faster switching speeds through optimised gate layout.

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{DSS}	Drain – Source Voltage	500	V
I_D	Continuous Drain Current	23	A
I_{DM}	Pulsed Drain Current ¹	84	A
V_{GS}	Gate – Source Voltage	± 30	V
V_{GSM}	Gate – Source Voltage Transient	± 40	
P_D	Total Power Dissipation @ $T_{case} = 25^{\circ}C$	235	W
	Derate Linearly	1.88	W/ $^{\circ}C$
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^{\circ}C$
T_L	Lead Temperature : 0.063" from Case for 10 Sec.	300	
I_{AR}	Avalanche Current ¹ (Repetitive and Non-Repetitive)	21	A
E_{AR}	Repetitive Avalanche Energy ¹	30	mJ
E_{AS}	Single Pulse Avalanche Energy ²	1300	

1) Repetitive Rating: Pulse Width limited by maximum junction temperature.

2) Starting $T_J = 25^{\circ}C$, $L = 5.90mH$, $R_G = 25\Omega$, Peak $I_L = 23A$

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

STATIC ELECTRICAL RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain – Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	500			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0V$)	$V_{DS} = V_{DSS}$			25	μA
		$V_{DS} = 0.8V_{DSS}, T_C = 125^{\circ}C$			250	
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 1.0mA$	2		4	V
$I_{D(ON)}$	On State Drain Current ²	$V_{DS} > I_{D(ON)} \times R_{DS(ON)}$ Max $V_{GS} = 10V$	23			A
$R_{DS(ON)}$	Drain – Source On State Resistance ²	$V_{GS} = 10V, I_D = 0.5 I_D [Cont.]$			0.20	Ω

DYNAMIC CHARACTERISTICS

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		3700	4440	pF
C_{oss}	Output Capacitance	$V_{DS} = 25V$		510	715	
C_{riss}	Reverse Transfer Capacitance	$f = 1MHz$		200	300	
Q_g	Total Gate Charge ³	$V_{GS} = 10V$		150	225	nC
Q_{gs}	Gate – Source Charge	$V_{DD} = 0.5 V_{DSS}$		25	37	
Q_{gd}	Gate – Drain (“Miller”) Charge	$I_D = I_D [Cont.] @ 25^{\circ}C$		70	105	
$t_{d(on)}$	Turn-on Delay Time	$V_{GS} = 15V$		12	25	ns
t_r	Rise Time	$V_{DD} = 0.5 V_{DSS}$		10	20	
$t_{d(off)}$	Turn-off Delay Time	$I_D = I_D [Cont.] @ 25^{\circ}C$		50	75	
t_f	Fall Time	$R_G = 1.6\Omega$		8	15	

SOURCE – DRAIN DIODE RATINGS AND CHARACTERISTICS

	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	(Body Diode)			23	A
I_{SM}	Pulsed Source Current ¹	(Body Diode)			84	
V_{SD}	Diode Forward Voltage ²	$V_{GS} = 0V, I_S = -I_D [Cont.]$			1.3	V
t_{rr}	Reverse Recovery Time	$I_S = -I_D [Cont.], di_S / dt = 100A/\mu s$		510		ns
Q_{rr}	Reverse Recovery Charge	$I_S = -I_D [Cont.], di_S / dt = 100A/\mu s$		10		μC

THERMAL CHARACTERISTICS

	Characteristic	Min.	Typ.	Max.	Unit
$R_{\theta JC}$	Junction to Case			0.53	$^{\circ}C/W$
$R_{\theta JA}$	Junction to Ambient			30	

1) Repetitive Rating: Pulse Width limited by maximum junction temperature.

2) Pulse Test: Pulse Width < 380 μs , Duty Cycle < 2%

3) See MIL-STD-750 Method 3471



CAUTION — Electrostatic Sensitive Devices. Anti-Static Procedures Must Be Followed.